





DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- . ESD Protected up to 2kV
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Qualified to AEC-Q101 standards for High Reliability

Mechanical Data

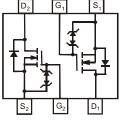
- Case: SOT-563
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Copper leadframe.
 Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.006 grams (approximate)





Top View





Bottom View

Top View Internal Schematic

Ordering Information (Note 3)

Part Number	Case	Packaging
DMN2400UV-7	SOT-563	3,000/Tape & Reel
DMN2400UV-13	SOT-563	10,000/Tape & Reel

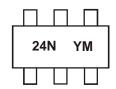
SOT-563

Notes: 1. No purposefully added lead.

2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com.

3. For packaging details, go to our website at http://www.diodes.com.

Marking Information



24N = Marking Code YM = Date Code Marking Y = Year (ex: W = 2009) M = Month (ex: 9 = September)

Date Code Key

Year	2009	9	2010		2011	20	12	2013		2014	2	2015
Code	W		Χ		Υ		7	Α		В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings @T_A = 25°C unless otherwise specified

Characterist		Symbol	Value	Units	
Drain-Source Voltage			V_{DSS}	20	V
Gate-Source Voltage			V _{GSS}	±12	V
Continuous Drain Current (Note 4) Steady $T_A = 25^{\circ}C$ State $T_A = 85^{\circ}C$		I _D	1.33 0.84	Α	
Pulsed Drain Current	Pulsed Drain Current			3	A

Thermal Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 4)	P_{D}	530	mW
Thermal Resistance, Junction to Ambient	$R_{ hetaJA}$	233.8	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

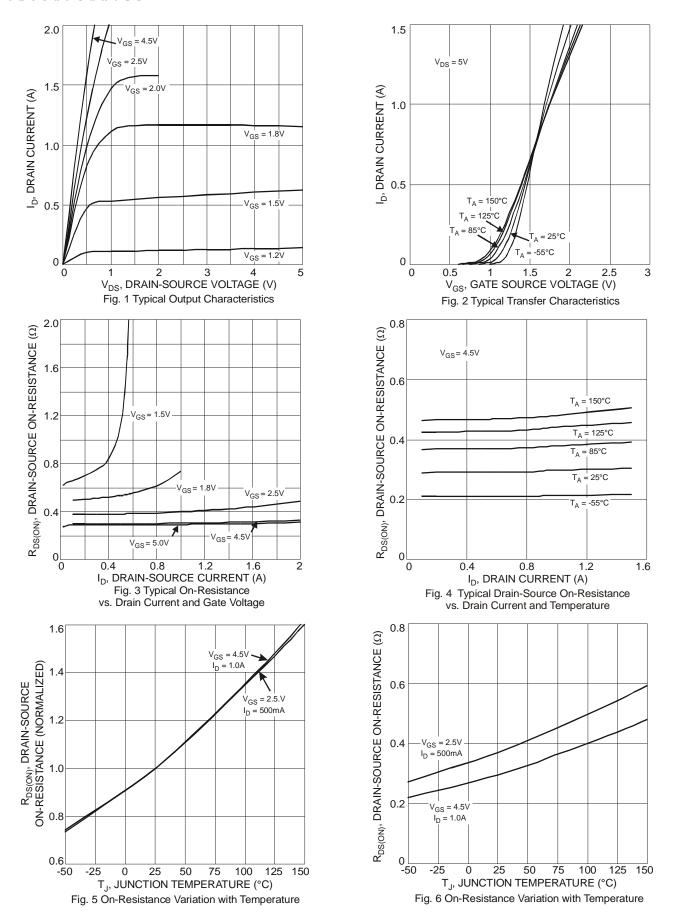
Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 5)								
Drain-Source Breakdown Voltage	BV _{DSS}	20	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$		
Zero Gate Voltage Drain Current T _J = 25°C	I _{DSS}	-	-	100	nA	$V_{DS} = 20V, V_{GS} = 0V$		
Gate-Source Leakage	I _{GSS}	-	-	±1.0	μА	$V_{GS} = \pm 4.5V, V_{DS} = 0V$		
Gale-Source Leakage		-	-	±50		$V_{GS} = \pm 10V, V_{DS} = 0V$		
ON CHARACTERISTICS (Note 5)								
Gate Threshold Voltage	$V_{GS(th)}$	0.5	-	0.9	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$		
		-	0.3	0.48		$V_{GS} = 5.0V, I_D = 200mA$		
		-	0.35	0.5		$V_{GS} = 4.5V, I_D = 600mA$		
Static Drain-Source On-Resistance	R _{DS} (ON)	-	0.45	0.7	Ω	$V_{GS} = 2.5V, I_D = 500mA$		
		-	0.55	0.9		$V_{GS} = 1.8V, I_D = 350mA$		
		-	0.65	1.5		$V_{GS} = 1.5V, I_D = 50mA$		
Forward Transfer Admittance	Y _{fs}	-	1.4	-	S	$V_{DS} = 10V, I_{D} = 400mA$		
Diode Forward Voltage (Note 5)	V _{SD}		0.7	1.2	V	$V_{GS} = 0V$, $I_S = 150mA$, $f = 1.0MHz$		
DYNAMIC CHARACTERISTICS (Note 6)								
Input Capacitance	C _{iss}	-	36.0	-	pF	101/1/		
Output Capacitance	Coss	-	5.7	-	pF	$V_{DS} = 16V, V_{GS} = 0V,$ - f = 1.0MHz		
Reverse Transfer Capacitance	C _{rss}	-	4.2	-	pF	1 = 1.000112		
Gate Resistance	Rg	-	68	-	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$,		
Total Gate Charge	Qg	-	0.5	-	nC	$V_{GS} = 4.5V, V_{DS} = 10V,$		
Gate-Source Charge	Q _{gs}	-	0.07	-	nC	I _D =250mA		
Gate-Drain Charge	Q_{gd}	-	0.1	-	nC			
Turn-On Delay Time	t _{D(on)}	-	4.06	-	ns	101/11/		
Turn-On Rise Time	t _r	-	7.28	-	ns	$V_{DD} = 10V, V_{GS} = 4.5V,$		
Turn-Off Delay Time	t _{D(off)}	-	13.74	-	ns	$R_L = 47\Omega, R_G = 10\Omega,$ $I_D = 200\text{mA}$		
Turn-Off Fall Time	t _f	-	10.54	-	ns	TID = ZUUITIA		

Notes:

- 4. Device soldered onto FR-4 PCB, minimum recommended soldering pad dimensions (25.4mm x 25.4mm x1.6mm, 2oz Cu pad: 0.18mm² x 6).
- 5. Short duration pulse test used to minimize self-heating effect.6. Guaranteed by design. Not subject to product testing.







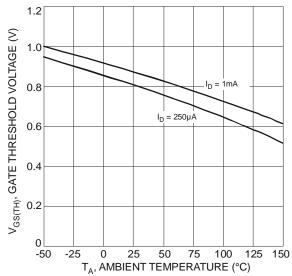
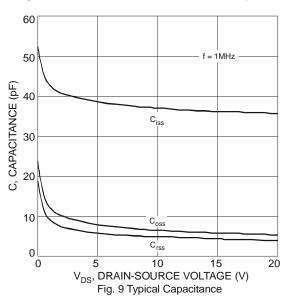
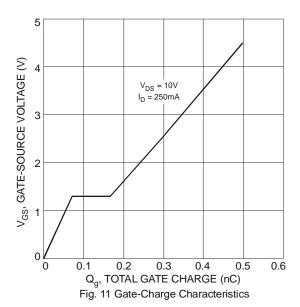
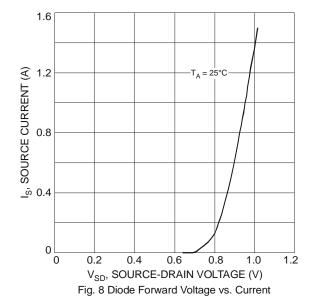


Fig. 7 Gate Threshold Variation vs. Ambient Temperature







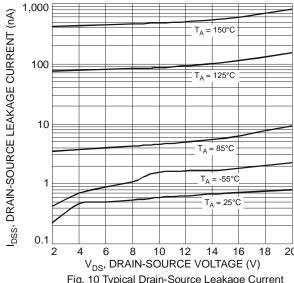
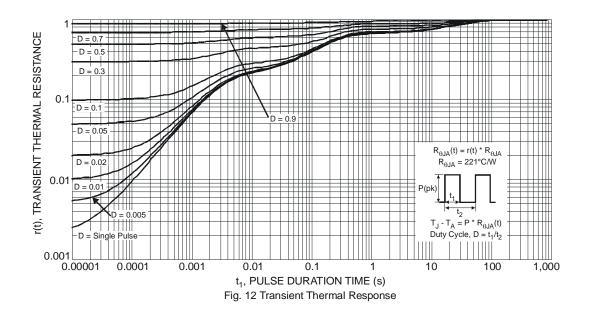
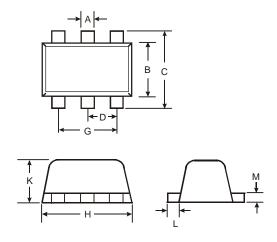


Fig. 10 Typical Drain-Source Leakage Current vs. Drain-Source Voltage



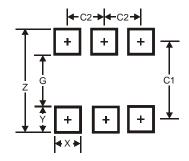


Package Outline Dimensions



SOT-563							
Dim	Min	Max	Тур				
A	0.15	0.30	0.20				
В	1.10	1.25	1.20				
O	1.55	1.70	1.60				
D	-	-	0.50				
G	0.90	1.10	1.00				
Н	1.50	1.70	1.60				
K	0.55	0.60	0.60				
L	0.10	0.30	0.20				
M	0.10	0.18	0.11				
All Dimensions in mm							

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.2
G	1.2
X	0.375
Υ	0.5
C1	1.7
C2	0.5



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